

2SD667, 2SD667A

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

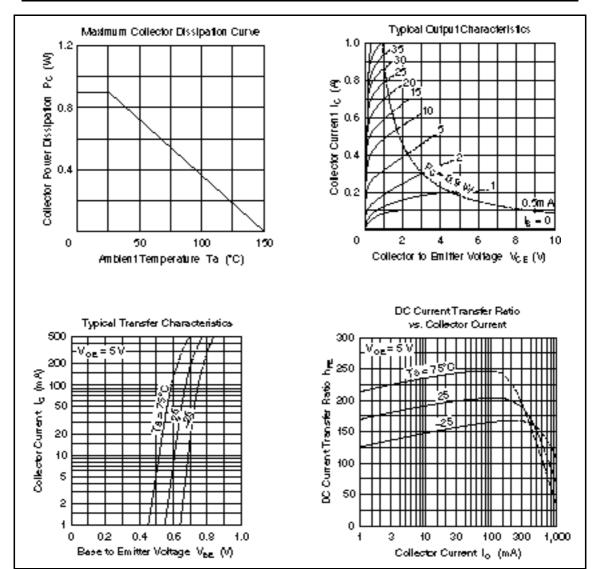
Item	Symbol	2SD667	2SD667A	Unit
Collector to base voltage	V _{CBO}	120	120	V
Collector to emitter voltage	V _{CEO}	80	100	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	1	1	А
Collector peak current	İ _{C(peak)}	2	2	А
Collector power dissipation	Pc	0.9	0.9	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	–55 to +150	–50 to +150	°C

Electrical Characteristics (Ta = 25°C)

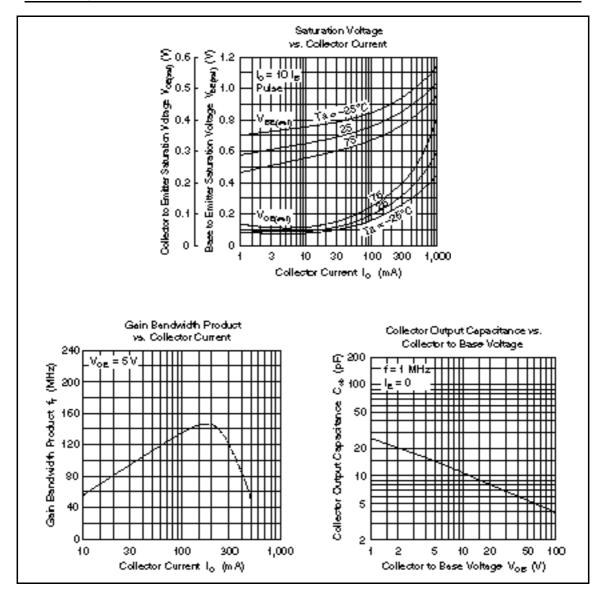
		2SD6	67		2SD6	67A			
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	120	_	_	120	_	_	V	$I_{c} = 10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	80	_	_	100	_	_	V	$I_c = 1 \text{ mA}, R_{\scriptscriptstyle BE} =$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	5	_	_	5	_	_	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}			10		_	10	μA	$V_{CB} = 100 \text{ V}, I_{E} = 0$
DC current transfer ratio	$h_{\rm FE1}^{*1}$	60	_	320	60	_	200		$V_{ce} = 5 V,$ $I_c = 150 \text{ mA}^{*2}$
	h_{FE2}	30	_	_	30	_	_		$V_{ce} = 5 V,$ $I_c = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	_	1	_	_	1	V	$I_{c} = 500 \text{ mA},$ $I_{B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	_	1.5	_	_	1.5	V	$V_{ce} = 5 V,$ $I_c = 150 \text{ mA}^{*2}$
Gain bandwidth product	f _T	—	140	_	_	140	_	MHz	$V_{ce} = 5 V,$ $I_c = 150 \text{ mA}^{*2}$
Collector output capacitance	Cob	—	12	—		12	—	pF	$V_{\rm CB} = 10 \text{ V}, \text{ I}_{\rm E} = 0,$ f = 1 MHz

_	В	С	D
2SD667	60 to 120	100 to 200	160 to 320
2SD667A	60 to 120	100 to 200	





2SD667, 2SD667A



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